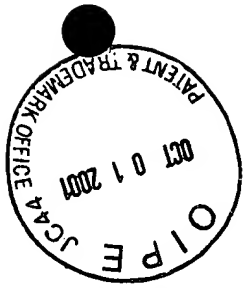
TSMC-01-133




September 26, 2001

2812

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject: Serial No. 09/905,408 07/16/01

Sheng Hsiung Chen, Mingh-Sing Tsai

SELECTIVE FORMATION OF METAL GATE FOR DUAL GATE OXIDE APPLICATION

Grp. Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 6,087,231 to Xiang et al., "Fabrication of Dual Gates of Field Transistors with Prevention of Reaction Between the Gate Electrode and the Gate Dielectric with a High Dielectric Constant," discloses a process for a dual gate.

The following three U.S. Patents reveal processes for dual gates and dummy gates:

1) U.S. Patent 6,159,782 to Xiang et al., "Fabrication of Field Effect Transistors Havaing Dual Gates with Gate Dielectrics of High Dielectric Constant."

2) U.S. Patent 5,960,270 to Misra et al., "Method for Forming an MOS Transistor Having a Metallic Gate Electrode that is Formed After the Formation of Self-Aligned Source and Drain Regions."

3) U.S. Patent 6,043,157 to Gardner et al., "Semiconductor Device Having Dual Gate Electrode Material and Process of Fabrication Thereof."

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

# INFORMATION DISCLOSURE CITATION IN AN APPLICATION

*(Use several sheets if necessary)*

| Docket Number (Optional) | Application Number |
|---|---|
| TSMC-[redacted]-133 | 09/905,408 |
| **Applicant** | |
| Sheng-Hsiung Chen et al. | |
| **Filing Date** | **Group Art Unit** |
| 07/16/01 | 2812 |

## U. S. PATENT DOCUMENTS

| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|---|---|---|---|---|---|---|
| | 6087231 | 7/11/00 | Xiang et al. | 438 | 287 | 8/5/99 |
| | 6159782 | 12/12/00 | Xiang et al. | 438 | 197 | 8/5/99 |
| | 5960270 | 9/28/99 | Misra et al. | 438 | 197 | 8/11/97 |
| | 6043157 | 3/28/00 | Gardner et al. | 438 | 692 | 12/18/97 |
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PATENT & TRADEMARK OFFICE JC44 OIPE OCT 01 2001

## FOREIGN PATENT DOCUMENTS

| | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | Translation YES | Translation NO |
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## OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

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| EXAMINER | DATE CONSIDERED |
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.